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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104fcafp-v0">https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104fcafp-v0</a>

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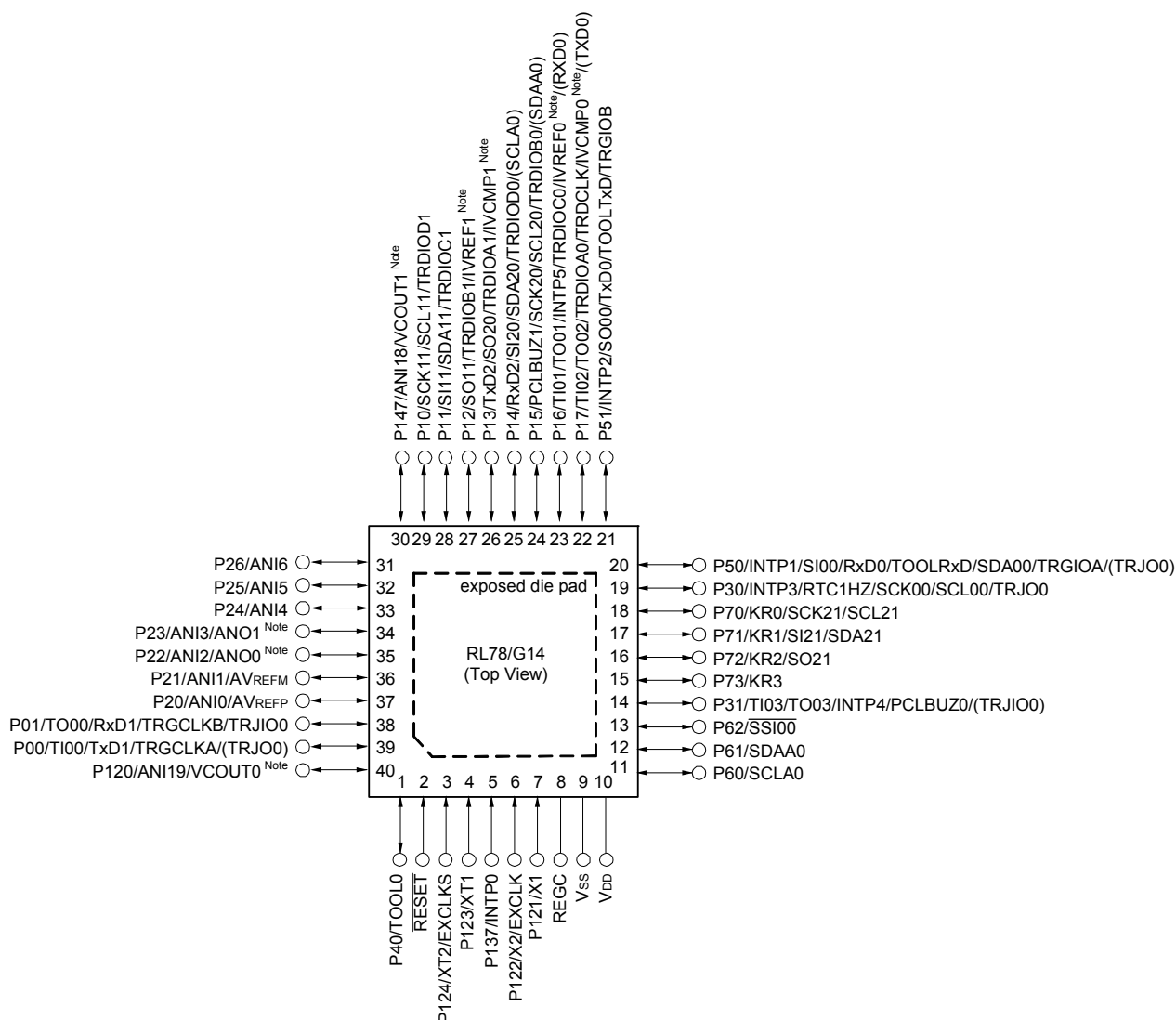
Pin count	Package	Fields of Application Note	Ordering Part Number
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	A	R5F104EAANA#U0, R5F104ECANA#U0, R5F104EDANA#U0, R5F104EEANA#U0, R5F104EFANA#U0, R5F104EGANA#U0, R5F104EHANA#U0 R5F104EAANA#W0, R5F104ECANA#W0, R5F104EDANA#W0, R5F104EEANA#W0, R5F104EFANA#W0, R5F104EGANA#W0, R5F104EHANA#W0
		D	R5F104EADNA#U0, R5F104ECDNA#U0, R5F104EDDNA#U0, R5F104EEDNA#U0, R5F104EFDNA#U0, R5F104EGDNA#U0, R5F104EHDNA#U0 R5F104EADNA#W0, R5F104ECDNA#W0, R5F104EDDNA#W0, R5F104EEDNA#W0, R5F104EFDNA#W0, R5F104EGDNA#W0, R5F104EHDNA#W0
		G	R5F104EAGNA#U0, R5F104ECGNA#U0, R5F104EDGNA#U0, R5F104EEGNA#U0, R5F104EFGNA#U0, R5F104EGGNA#U0, R5F104EHGNA#U0 R5F104EAGNA#W0, R5F104ECGNA#W0, R5F104EDGNA#W0, R5F104EEGNA#W0, R5F104EFGNA#W0, R5F104EGGNA#W0, R5F104EHGNA#W0
44 pins	44-pin plastic LQFP (10 × 10, 0.8 mm pitch)	A	R5F104FAAFP#V0, R5F104FCAFP#V0, R5F104FDAFP#V0, R5F104FEAFP#V0, R5F104FFAFP#V0, R5F104FGAFP#V0, R5F104FHAFP#V0, R5F104FJAFP#V0 R5F104FAAFP#X0, R5F104FCAFP#X0, R5F104FDAFP#X0, R5F104FEAFP#X0, R5F104FFAFP#X0, R5F104FGAFP#X0, R5F104FHAFP#X0, R5F104FJAFP#X0
		D	R5F104FADFP#V0, R5F104FCDFP#V0, R5F104FDDFP#V0, R5F104FEDFP#V0, R5F104FFDFP#V0, R5F104FGDFP#V0, R5F104FHDFP#V0, R5F104FJDFP#V0 R5F104FADFP#X0, R5F104FCDFP#X0, R5F104FDDFP#X0, R5F104FEDFP#X0, R5F104FFDFP#X0, R5F104FGDFP#X0, R5F104FHDFP#X0, R5F104FJDFP#X0
		G	R5F104FAGFP#V0, R5F104FCGFP#V0, R5F104FDGFP#V0, R5F104FEGFP#V0, R5F104FFGFP#V0, R5F104FGGFP#V0, R5F104FHGFP#V0, R5F104FJGFP#V0 R5F104FAGFP#X0, R5F104FCGFP#X0, R5F104FDGFP#X0, R5F104FEGFP#X0, R5F104FFGFP#X0, R5F104FGGFP#X0, R5F104FHGFP#X0, R5F104FJGFP#X0

**Note** For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

**Caution** The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

### 1.3.4 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



**Note** Mounted on the 96 KB or more code flash memory products.

**Caution** Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

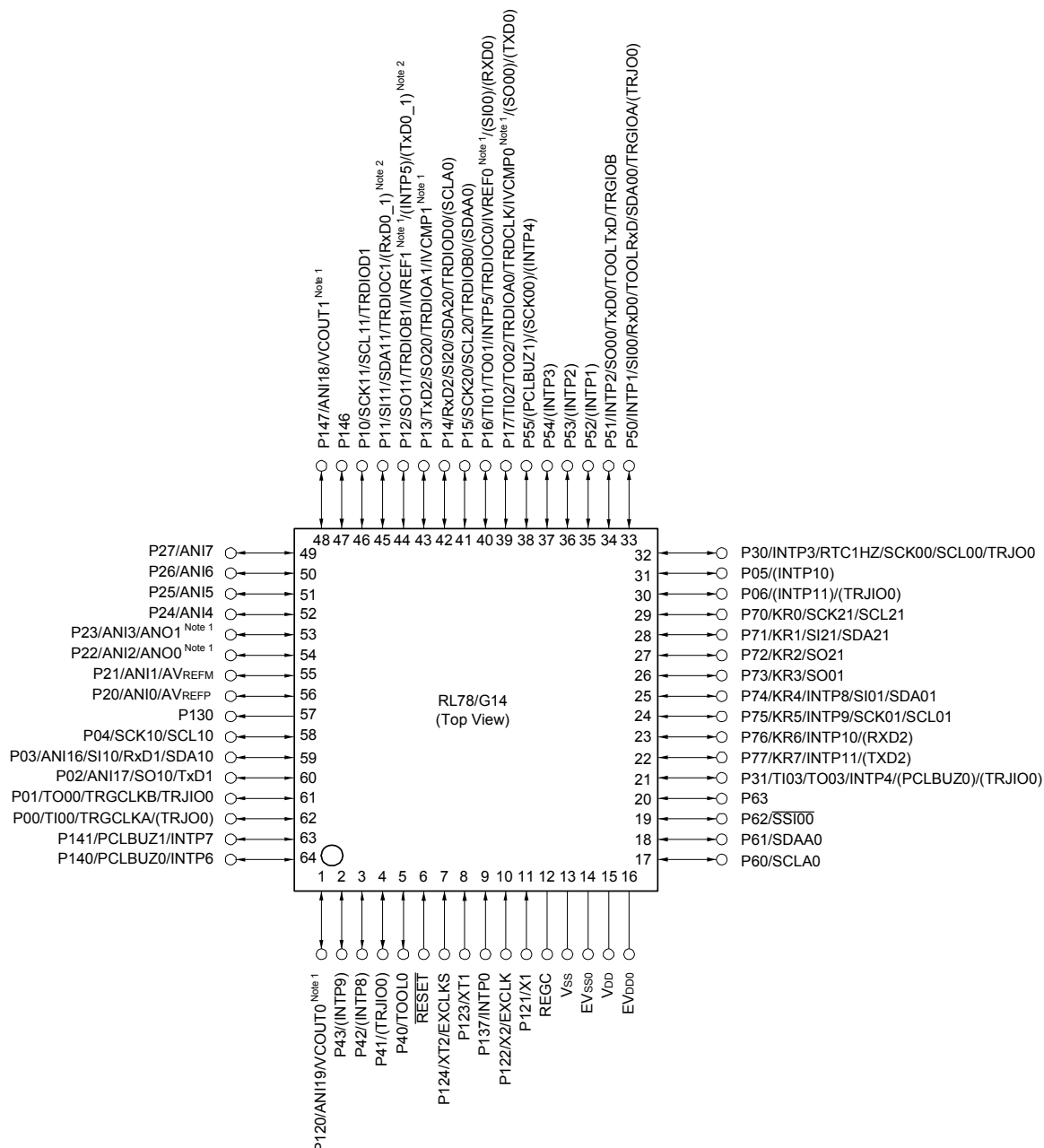
**Remark 1.** For pin identification, see 1.4 Pin Identification.

**Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

**Remark 3.** It is recommended to connect an exposed die pad to Vss.

### 1.3.8 64-pin products

- 64-pin plastic LQFP (14 × 14 mm, 0.8 mm pitch)
- 64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)



**Note 1.** Mounted on the 96 KB or more code flash memory products.

**Note 2.** Mounted on the 384 KB or more code flash memory products.

**Caution 1.** Make EVss0 pin the same potential as Vss pin.

**Caution 2.** Make VDD pin the potential that is higher than EVDD0 pin.

**Caution 3.** Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

**Remark 1.** For pin identification, see 1.4 Pin Identification.

**Remark 2.** When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.

**Remark 3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

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Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)
Clock output/buzzer output		2	2	2	2
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f <sub>MAIN</sub> = 20 MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f <sub>MAIN</sub> = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f <sub>SUB</sub> = 32.768 kHz operation)			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I <sup>2</sup> C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I <sup>2</sup> C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I <sup>2</sup> C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I <sup>2</sup> C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I <sup>2</sup> C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels			
	I <sup>2</sup> C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		28 sources			29 sources
Event link controller (ELC)		Event input: 19 Event trigger output: 7			Event input: 20 Event trigger output: 7
Vectored interrupt sources	Internal	24	24	24	24
	External	6	6	6	7
Key interrupt		—	—	—	4
Reset		<ul style="list-style-type: none"> <li>• Reset by <math>\overline{\text{RESET}}</math> pin</li> <li>• Internal reset by watchdog timer</li> <li>• Internal reset by power-on-reset</li> <li>• Internal reset by voltage detector</li> <li>• Internal reset by illegal instruction execution <sup>Note</sup></li> <li>• Internal reset by RAM parity error</li> <li>• Internal reset by illegal-memory access</li> </ul>			
Power-on-reset circuit		<ul style="list-style-type: none"> <li>• Power-on-reset:    1.51 ±0.04 V (T<sub>A</sub> = −40 to +85°C)                                1.51 ±0.06 V (T<sub>A</sub> = −40 to +105°C)</li> <li>• Power-down-reset: 1.50 ±0.04 V (T<sub>A</sub> = −40 to +85°C)                                1.50 ±0.06 V (T<sub>A</sub> = −40 to +105°C)</li> </ul>			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		V <sub>DD</sub> = 1.6 to 5.5 V (T <sub>A</sub> = −40 to +85°C) V <sub>DD</sub> = 2.4 to 5.5 V (T <sub>A</sub> = −40 to +105°C)			
Operating ambient temperature		T <sub>A</sub> = −40 to +85°C (A: Consumer applications, D: Industrial applications), T <sub>A</sub> = −40 to +105°C (G: Industrial applications)			

**Note** The illegal instruction is generated when instruction code FFH is executed.  
Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

**Absolute Maximum Ratings****(2/2)**

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	IOH1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	IOH2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	TA	In normal operation mode		-40 to +85	°C
		In flash memory programming mode			
Storage temperature	Tstg			-65 to +150	°C

**Caution** Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

## (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit			
Supply current Note 1	IDD2 Note 2	HALT mode	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.79	3.32	mA			
					VDD = 3.0 V		0.79	3.32				
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.49	2.63				
					VDD = 3.0 V		0.49	2.63				
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.62	2.57				
					VDD = 3.0 V		0.62	2.57				
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.4	2.00				
					VDD = 3.0 V		0.4	2.00				
				fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.38	1.49				
					VDD = 3.0 V		0.38	1.49				
				LS (low-speed main) mode Note 7	fHOCO = 8 MHz, fIH = 8 MHz Note 4	VDD = 3.0 V		250		800	μA	
						VDD = 2.0 V		250		800		
				LV (low-voltage main) mode Note 7	fHOCO = 4 MHz, fIH = 4 MHz Note 4	VDD = 3.0 V		420		755	μA	
						VDD = 2.0 V		420		755		
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.30	1.63	mA			
					Resonator connection		0.40	1.85				
					fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.30		1.63		
						Resonator connection		0.40		1.85		
					fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.20		0.89		
						Resonator connection		0.25		0.97		
					fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.20		0.89		
						Resonator connection		0.25		0.97		
				LS (low-speed main) mode Note 7	fMX = 8 MHz Note 3, VDD = 3.0 V	Square wave input		110	580	μA		
						Resonator connection		140	630			
					fMX = 8 MHz Note 3, VDD = 2.0 V	Square wave input		110	580			
						Resonator connection		140	630			
				Subsystem clock operation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.28	0.66	μA		
						Resonator connection		0.47	0.85			
			fSUB = 32.768 kHz Note 5, TA = +25°C		Square wave input		0.34	0.66				
					Resonator connection		0.53	0.85				
			fSUB = 32.768 kHz Note 5, TA = +50°C		Square wave input		0.37	2.35				
					Resonator connection		0.56	2.54				
			fSUB = 32.768 kHz Note 5, TA = +70°C		Square wave input		0.61	4.08				
					Resonator connection		0.80	4.27				
			fSUB = 32.768 kHz Note 5, TA = +85°C		Square wave input		1.55	8.09				
					Resonator connection		1.74	8.28				
			IDD3 Note 6	STOP mode Note 8	TA = -40°C					0.19	0.57	μA
					TA = +25°C					0.25	0.57	
					TA = +50°C					0.33	2.26	
					TA = +70°C					0.52	3.99	
					TA = +85°C					1.46	8.00	

(Notes and Remarks are listed on the next page.)

**(4) Peripheral Functions (Common to all products)****(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	IFIL Note 1				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	IIIT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 5	fIL = 15 kHz			0.22		μA
A/D converter operating current	IADC Notes 1, 6	When conversion at maximum speed	Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
			Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
D/A converter operating current	IDAC Notes 1, 11, 13	Per D/A converter channel				1.5	mA
Comparator operating current	ICMP Notes 1, 12, 13	VDD = 5.0 V, Regulator output voltage = 2.1 V	Window mode		12.5		μA
			Comparator high-speed mode		6.5		μA
			Comparator low-speed mode		1.7		μA
		VDD = 5.0 V, Regulator output voltage = 1.8 V	Window mode		8.0		μA
			Comparator high-speed mode		4.0		μA
			Comparator low-speed mode		1.3		μA
LVD operating current	ILVD Notes 1, 7				0.08		μA
Self-programming operating current	IFSP Notes 1, 9				2.50	12.20	mA
BGO operating current	IBGO Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	1.44	
		CSI/UART operation			0.70	0.84	
		DTC operation			3.10		

**Note 1.** Current flowing to VDD.**Note 2.** When high speed on-chip oscillator and high-speed system clock are stopped.**Note 3.** Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.**Note 4.** Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.

**(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)**

**(TA = -40 to +85°C, 2.7 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t <sub>KCY1</sub>	t <sub>KCY1</sub> ≥ 2/f <sub>CLK</sub>	4.0 V ≤ EVDD0 ≤ 5.5 V	62.5		250		500		ns
			2.7 V ≤ EVDD0 ≤ 5.5 V	83.3		250		500		ns
SCKp high-/low-level width	t <sub>KH1</sub> , t <sub>KL1</sub>	4.0 V ≤ EVDD0 ≤ 5.5 V		t <sub>KCY1</sub> /2 - 7		t <sub>KCY1</sub> /2 - 50		t <sub>KCY1</sub> /2 - 50		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		t <sub>KCY1</sub> /2 - 10		t <sub>KCY1</sub> /2 - 50		t <sub>KCY1</sub> /2 - 50		ns
Slp setup time (to SCKp↑) Note 1	t <sub>SIK1</sub>	4.0 V ≤ EVDD0 ≤ 5.5 V		23		110		110		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		33		110		110		ns
Slp hold time (from SCKp↑) Note 2	t <sub>SI1</sub>	2.7 V ≤ EVDD0 ≤ 5.5 V		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	t <sub>SO1</sub>	C = 20 pF Note 4			10		10		10	ns

**Note 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

**Note 2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

**Note 3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

**Note 4.** C is the load capacitance of the SCKp and SOp output lines.

**Caution** Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**Remark 1.** This value is valid only when CSI00's peripheral I/O redirect function is not used.

**Remark 2.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),  
g: PIM and POM numbers (g = 1)

**Remark 3.** f<sub>MCK</sub>: Serial array unit operation clock frequency  
(Operation clock to be set by the CKS<sub>mn</sub> bit of serial mode register mn (SMR<sub>mn</sub>). m: Unit number,  
n: Channel number (mn = 00))

**(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)****(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)****(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V			Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 1.4 kΩ, Vb = 2.7 V			2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V			Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 2.7 kΩ, Vb = 2.3 V			1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V			Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 5.5 kΩ, Vb = 1.6 V			0.43 Note 7		0.43 Note 7	Mbps

**Note 1.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.  
Expression for calculating the transfer rate when 4.0 V ≤ EVDD0 ≤ 5.5 V and 2.7 V ≤ Vb ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

\* This value is the theoretical value of the relative difference between the transmission and reception sides

**Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met.  
Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

**Note 3.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EVDD0 < 4.0 V and 2.3 V ≤ Vb ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

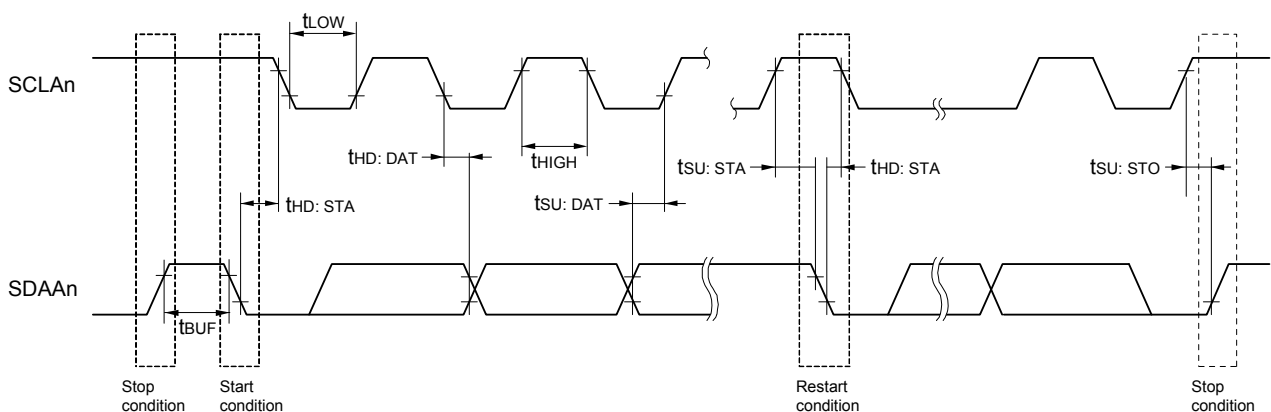
\* This value is the theoretical value of the relative difference between the transmission and reception sides

**(3) I<sup>2</sup>C fast mode plus****(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fSCL	Fast mode plus: fCLK ≥ 10 MHz 2.7 V ≤ EVDD0 ≤ 5.5 V	0	1000	—	—	—	—	kHz
Setup time of restart condition	tSU: STA	2.7 V ≤ EVDD0 ≤ 5.5 V	0.26		—	—	—	—	μs
Hold time Note 1	tHD: STA	2.7 V ≤ EVDD0 ≤ 5.5 V	0.26		—	—	—	—	μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EVDD0 ≤ 5.5 V	0.5		—	—	—	—	μs
Hold time when SCLA0 = "H"	tHIGH	2.7 V ≤ EVDD0 ≤ 5.5 V	0.26		—	—	—	—	μs
Data setup time (reception)	tSU: DAT	2.7 V ≤ EVDD0 ≤ 5.5 V	50		—	—	—	—	ns
Data hold time (transmission) Note 2	tHD: DAT	2.7 V ≤ EVDD0 ≤ 5.5 V	0	0.45	—	—	—	—	μs
Setup time of stop condition	tSU: STO	2.7 V ≤ EVDD0 ≤ 5.5 V	0.26		—	—	—	—	μs
Bus-free time	tBUF	2.7 V ≤ EVDD0 ≤ 5.5 V	0.5		—	—	—	—	μs

**Note 1.** The first clock pulse is generated after this period when the start/restart condition is detected.**Note 2.** The maximum value (MAX.) of tHD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.**Caution** The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.**Note 3.** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: Cb = 120 pF, Rb = 1.1 kΩ

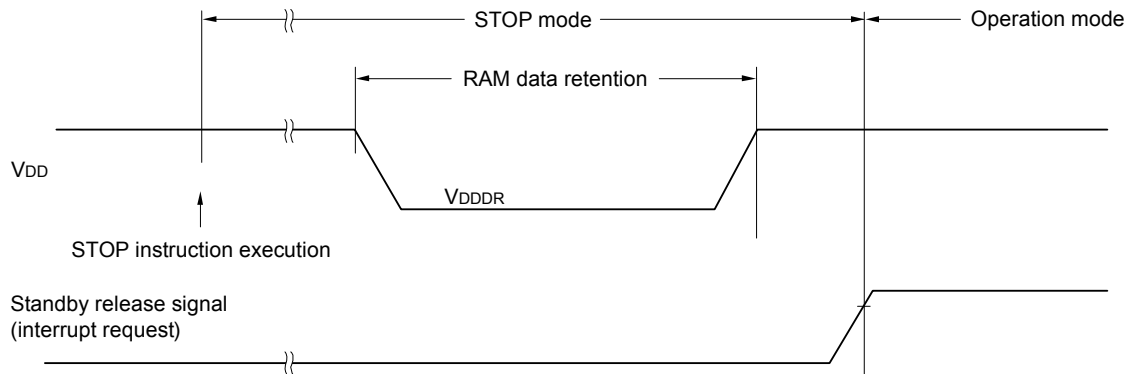
**I<sup>2</sup>C serial transfer timing****Remark** n = 0, 1

## 2.7 RAM Data Retention Characteristics

(TA = -40 to +85°C, VSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 <small>Note</small>		5.5	V

**Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



## 2.8 Flash Memory Programming Characteristics

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fCLK	1.8 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites <small>Notes 1, 2, 3</small>	C <sub>erwr</sub>	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites <small>Notes 1, 2, 3</small>		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

**Note 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

**Note 2.** When using flash memory programmer and Renesas Electronics self-programming library

**Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

## 2.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +85°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

- Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or VSS, EVSS0, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3.** When high-speed system clock and subsystem clock are stopped.
- Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.  
 HS (high-speed main) mode:  $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$   
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$

**Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

**Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)

**Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)

**Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)

**Remark 5.** Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

- Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or VSS, EVSS0, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** During HALT instruction execution by flash memory.
- Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4.** When high-speed system clock and subsystem clock are stopped.
- Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6.** Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.  
 HS (high-speed main) mode:  $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$   
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
- Note 8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

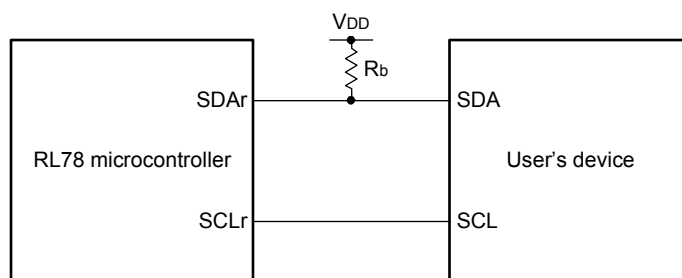
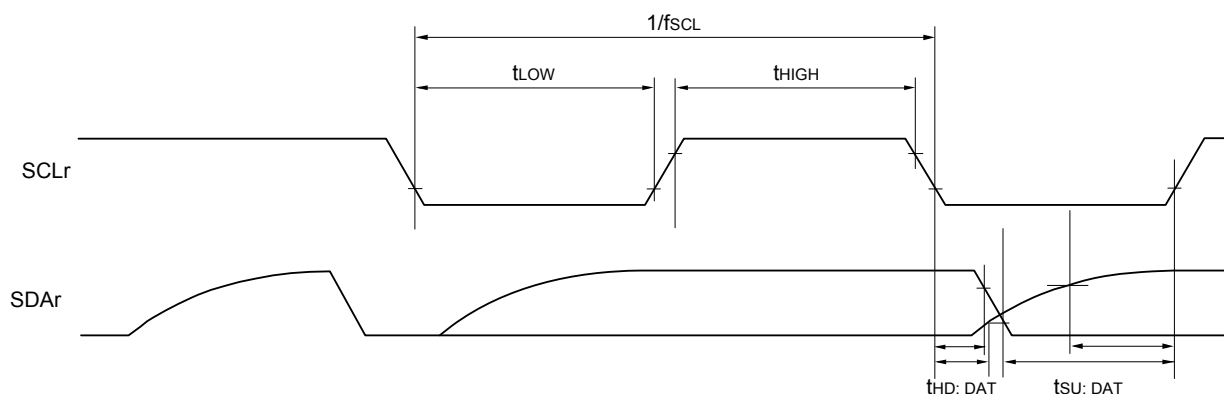
**(4) During communication at same potential (simplified I<sup>2</sup>C mode)****(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f <sub>SCL</sub>	2.7 V ≤ EVDD0 ≤ 5.5 V, Cb = 50 pF, Rb = 2.7 kΩ		400 Note 1	kHz
		2.4 V ≤ EVDD0 ≤ 5.5 V, Cb = 100 pF, Rb = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = "L"	t <sub>LOW</sub>	2.7 V ≤ EVDD0 ≤ 5.5 V, Cb = 50 pF, Rb = 2.7 kΩ	1200		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V, Cb = 100 pF, Rb = 3 kΩ	4600		ns
Hold time when SCLr = "H"	t <sub>HIGH</sub>	2.7 V ≤ EVDD0 ≤ 5.5 V, Cb = 50 pF, Rb = 2.7 kΩ	1200		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V, Cb = 100 pF, Rb = 3 kΩ	4600		ns
Data setup time (reception)	t <sub>SU: DAT</sub>	2.7 V ≤ EVDD0 ≤ 5.5 V, Cb = 50 pF, Rb = 2.7 kΩ	1/f <sub>MCK</sub> + 220 Note 2		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V, Cb = 100 pF, Rb = 3 kΩ	1/f <sub>MCK</sub> + 580 Note 2		ns
Data hold time (transmission)	t <sub>HD: DAT</sub>	2.7 V ≤ EVDD0 ≤ 5.5 V, Cb = 50 pF, Rb = 2.7 kΩ	0	770	ns
		2.4 V ≤ EVDD0 ≤ 5.5 V, Cb = 100 pF, Rb = 3 kΩ	0	1420	ns

**Note 1.** The value must also be equal to or less than f<sub>MCK</sub>/4.**Note 2.** Set the f<sub>MCK</sub> value to keep the hold time of SCLr = "L" and SCLr = "H".

**Caution** Select the normal input buffer and the N-ch open drain output (V<sub>DD</sub> tolerance (for the 30- to 52-pin products)/EV<sub>DD</sub> tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

**Simplified I<sup>2</sup>C mode connection diagram (during communication at same potential)****Simplified I<sup>2</sup>C mode serial transfer timing (during communication at same potential)**

**Remark 1.**  $R_b[\Omega]$ : Communication line (SDAr) pull-up resistance,  $C_b[F]$ : Communication line (SDAr, SCLr) load capacitance

**Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 3 to 5, 14),  
h: POM number (h = 0, 1, 3 to 5, 7, 14)

**Remark 3.**  $f_{MCK}$ : Serial array unit operation clock frequency  
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),  
n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

**(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)****( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$ ,  $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$ )****(1/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Transfer rate		reception	$4.0\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$ , $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$	$f_{\text{MCK}}/12$ Note 1	bps
			Theoretical value of the maximum transfer rate $f_{\text{MCK}} = f_{\text{CLK}}$ Note 3	2.6	Mbps
			$2.7\text{ V} \leq \text{EVDD0} < 4.0\text{ V}$ , $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$	$f_{\text{MCK}}/12$ Note 1	bps
			Theoretical value of the maximum transfer rate $f_{\text{MCK}} = f_{\text{CLK}}$ Note 3	2.6	Mbps
			$2.4\text{ V} \leq \text{EVDD0} < 3.3\text{ V}$ , $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$	$f_{\text{MCK}}/12$ Notes 1, 2	bps
			Theoretical value of the maximum transfer rate $f_{\text{MCK}} = f_{\text{CLK}}$ Note 3	2.6	Mbps

**Note 1.** Transfer rate in the SNOOZE mode is 4800 bps only.However, the SNOOZE mode cannot be used when  $\text{FRQSEL4} = 1$ .**Note 2.** The following conditions are required for low voltage interface when  $\text{EVDD0} < \text{VDD}$ . $2.4\text{ V} \leq \text{EVDD0} < 2.7\text{ V}$ : MAX. 1.3 Mbps**Note 3.** The maximum operating frequencies of the CPU/peripheral hardware clock ( $f_{\text{CLK}}$ ) are:HS (high-speed main) mode: 32 MHz ( $2.7\text{ V} \leq \text{VDD} \leq 5.5\text{ V}$ )16 MHz ( $2.4\text{ V} \leq \text{VDD} \leq 5.5\text{ V}$ )

**Caution** Select the TTL input buffer for the RxDq pin and the N-ch open drain output ( $\text{VDD}$  tolerance (for the 30- to 52-pin products)/ $\text{EVDD}$  tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For  $V_{\text{IH}}$  and  $V_{\text{IL}}$ , see the DC characteristics with TTL input buffer selected.

**Remark 1.**  $V_b$  [V]: Communication line voltage**Remark 2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)**Remark 3.**  $f_{\text{MCK}}$ : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

**Remark 4.** UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

**Note 5.** The smaller maximum transfer rate derived by using  $f_{MCK}/12$  or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when  $2.4\text{ V} \leq E_{VDD0} < 3.3\text{ V}$  and  $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

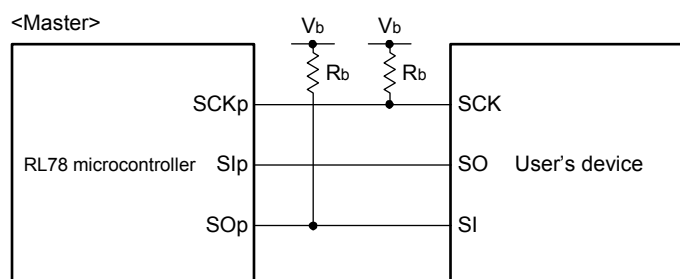
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

\* This value is the theoretical value of the relative difference between the transmission and reception sides

**Note 6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.

**Caution** Select the TTL input buffer for the RxDq pin and the N-ch open drain output ( $V_{DD}$  tolerance (for the 30- to 52-pin products)/ $E_{VDD}$  tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For  $V_{IH}$  and  $V_{IL}$ , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

**CSI mode connection diagram (during communication at different potential)**

**Remark 5.**  $R_b[\Omega]$ : Communication line (SCKp, SOp) pull-up resistance,  $C_b[F]$ : Communication line (SCKp, SOp) load capacitance,  $V_b[V]$ : Communication line voltage

**Remark 6.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

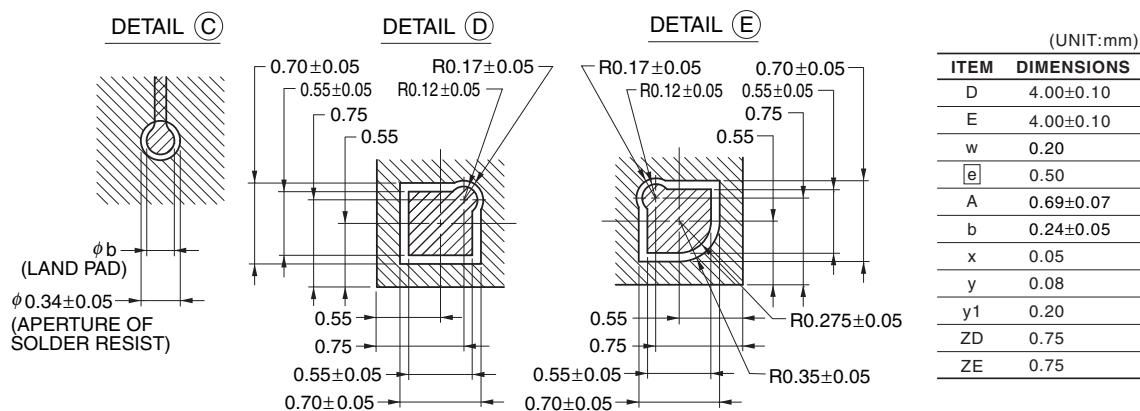
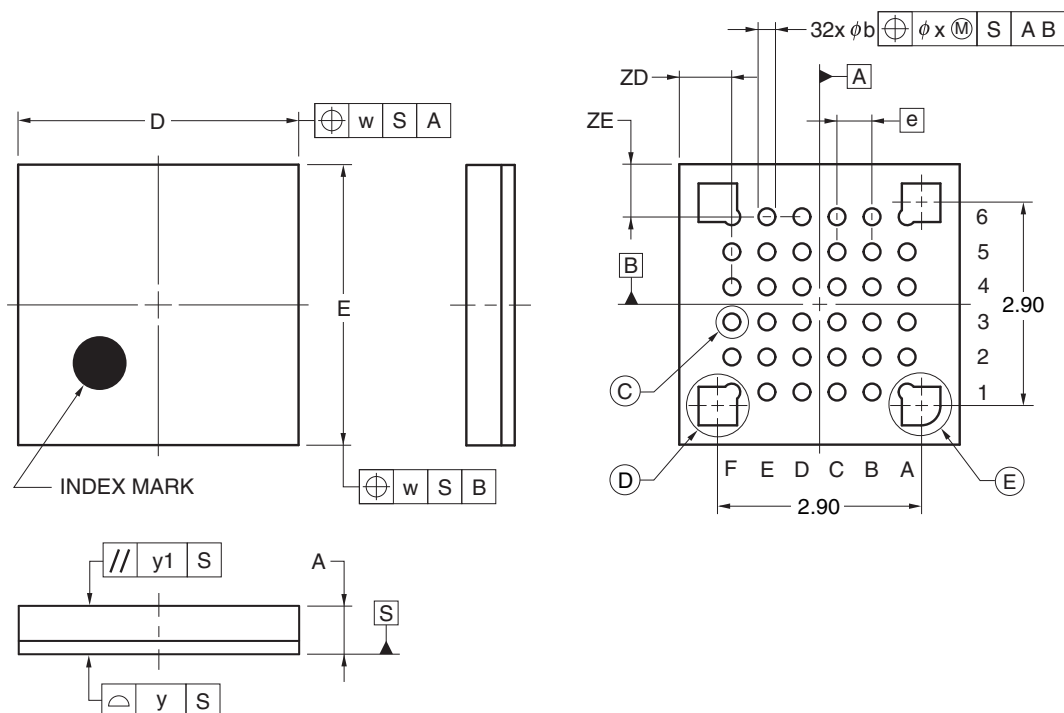
**Remark 7.**  $f_{MCK}$ : Serial array unit operation clock frequency  
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

**Remark 8.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

### 4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA  
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



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